

# Exhibit A

## Invention Disclosure

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Full Name(s) of Inventor(s)		Employee No.	Department	Dept. Code	Tel No.	For Use by IP Law Disclosure No.
English	Chinese					Received Date (Time Stamp)
HMChen	陳惠生	058	TEPM			M6G02-005
CKChou						
JYLee	劉盈玲	006				
HTLiu						

### Title of Invention -

- English: A Clean process for finishing IC product
- Chinese

### Background Information - Current Practice and Disadvantages

All the final process steps of metal pad or metal bump are chemical process in the current IC process.

There is micro-contamination absorbed on the final metal surface.

Over killed problem happen sometimes during chip probing due to micro-contamination on metal pad.

### Main Points of Claim (Please List Item by Item)

Add in a physical clean after finish IC process before chip probing.

The physical clean can be a inner gas plasma, sputtering etch, ion mill or any bombardment clean.

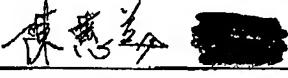
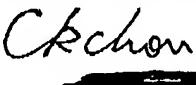
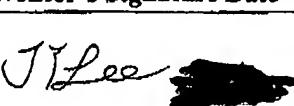
### Problem Solved or Improvements Obtained by this Invention (Please List Item by Item)

To reduce over killed problem during chip probing.

### Keyword Search for Patent/Literatures

### Patent/Literatures Search Result (Please Specify Similar Patent No. and Literature Citation)

### Detailed Description of Invention - (Continued Next Page)

Witnesses: The Two Witnesses whose Signatures appear below have <u>Read and Understand</u> this Entire Invention Disclosure.		Disclosure Submitted by	
Signature of Witness	Date	Inventor's Signature Date	Inventor's Signature Date
			
Eric Lin			
Signature of Witness	Date	Inventor's Signature Date	Inventor's Signature Date
陳盈玲			

# Invention Disclosure

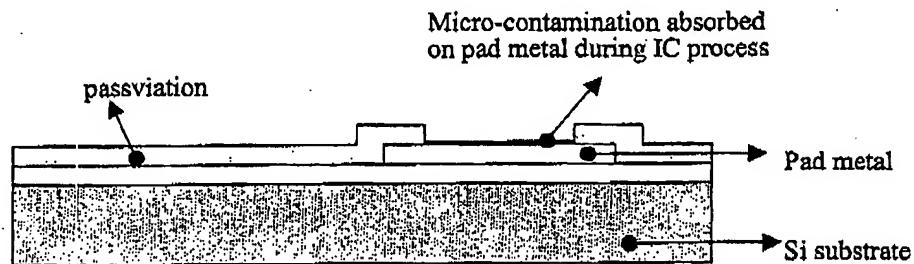
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## Detailed Description of Invention – Continued

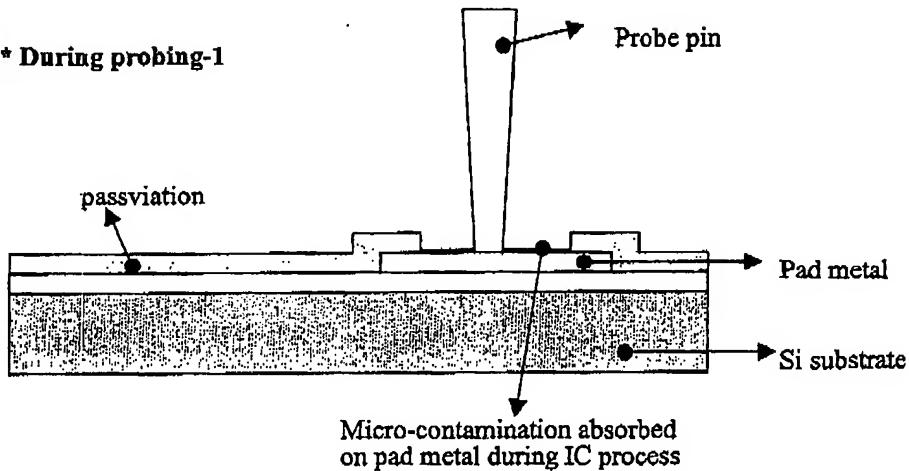
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MES 02 - 005

### Current practice 1:

\* After finish IC process



\* During probing-1



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have Read and Understand this  
Entire Invention Disclosure.**

### Disclosure Submitted by

Signature of Witness      Date

*Erz L.*

Inventor's Signature Date

*陳惠生*

Inventor's Signature Date

*Ck chon*

Signature of Witness      Date

*陳盈智*

Inventor's Signature Date

*J Lee*

Inventor's Signature Date

*Ht Lin*

# Invention Disclosure

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## Detailed Description of Invention – Continued

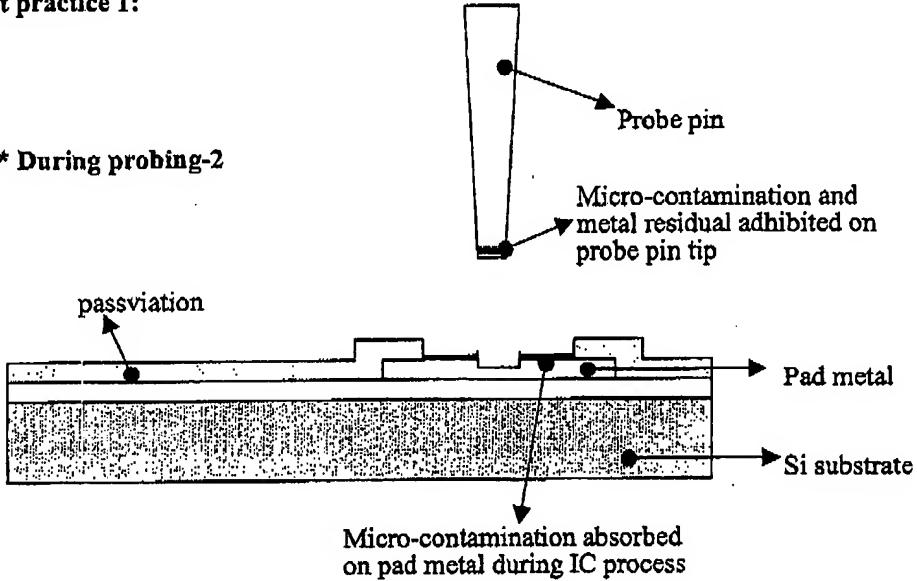
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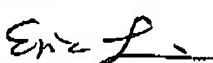
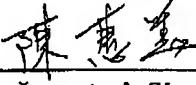
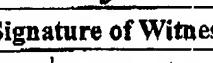
Disclosure No.

1A6902-005

Current practice 1:

\* During probing-2



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		Inventor's Signature Date	Inventor's Signature Date
			
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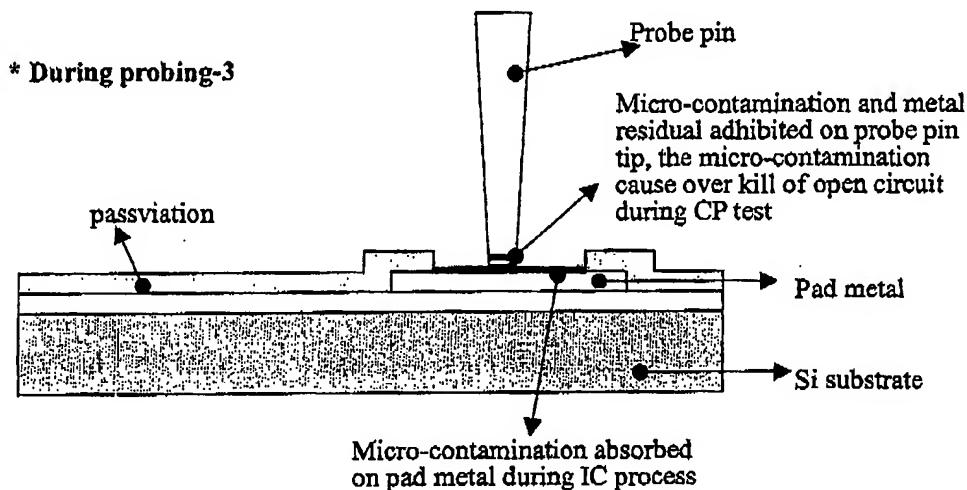
## Detailed Description of Invention – Continued

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Disclosure No.

MEG02-005

### Current practice 1:



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Signature of Witness	Date	Inventor's Signature Date	Inventor's Signature Date
<u>Eric Li</u>		<u>陳惠生</u>	<u>Ckchon</u>
		Inventor's Signature Date	Inventor's Signature Date
<u>JT Lee</u>		<u>JT Lee</u>	<u>Ht Lin</u>



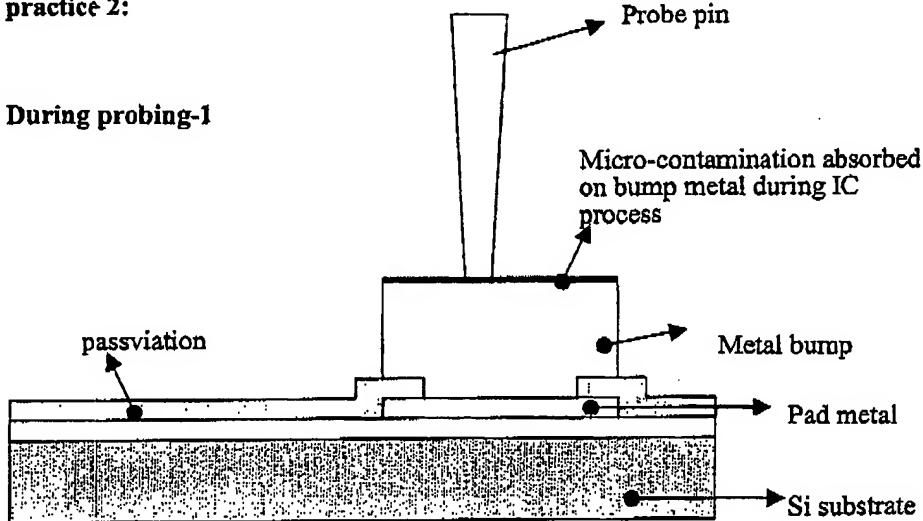
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Detailed Description of Invention – Continued	For Use by IP Law Disclosure No. MEG02-005
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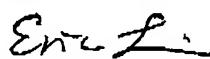
Current practice 2:

\* During probing-1

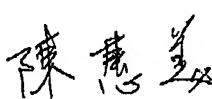
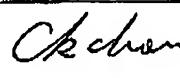


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Signature of Witness      Date



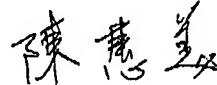
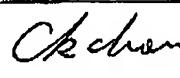
Signature of Witness      Date

   
陳 惠 球

Disclosure Submitted by

Inventor's Signature Date

Inventor's Signature Date

   
陳 惠 球

Inventor's Signature Date

   
JY Lee

Inventor's Signature Date

**Invention Disclosure**

Confidential ( When Completed )

**Detailed Description of Invention – Continued**

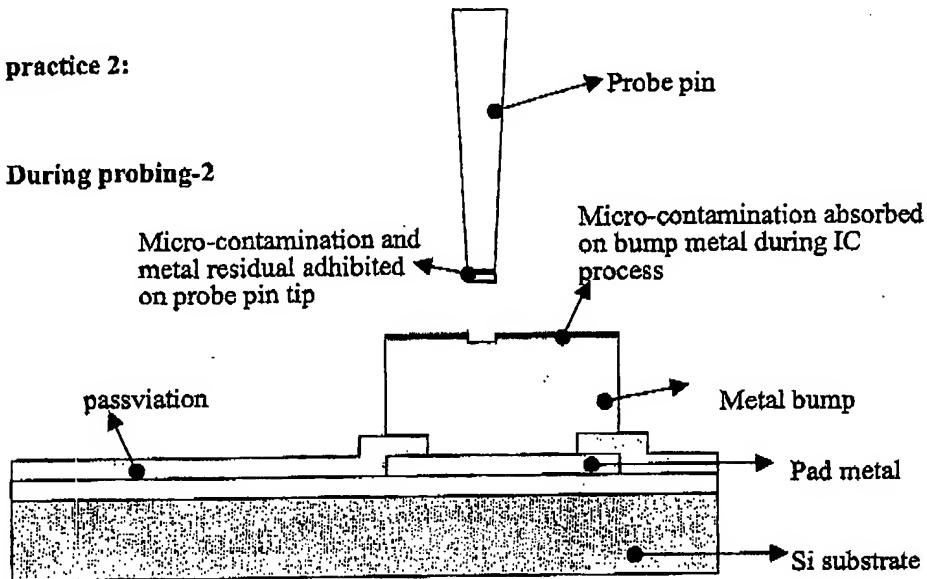
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Disclosure No.

MEG02-005

**Current practice 2:**

\* During probing-2



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Entire Invention Disclosure.**

**Signature of Witness      Date**

*Eric Lee*

**Disclosure Submitted by**

**Inventor's Signature Date**

*J.Y. Lee*

**Inventor's Signature Date**

*Ckchan*

**Signature of Witness      Date**

*陳盈智*

**Inventor's Signature Date**

*JYLee*

**Inventor's Signature Date**

*H.T.Liu*

# Invention Disclosure

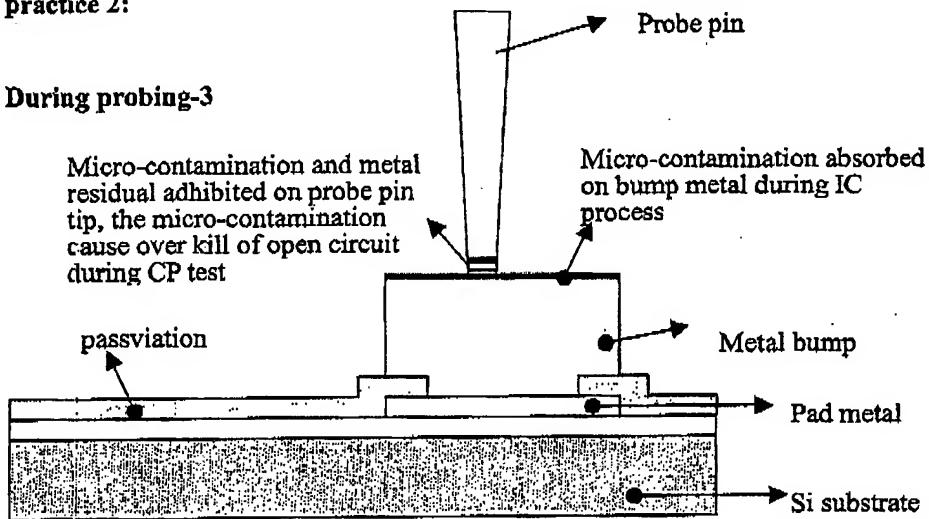
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## Current practice 2:

### \* During probing-3

Micro-contamination and metal residual exhibited on probe pin tip, the micro-contamination cause over kill of open circuit during CP test



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**Signature of Witness      Date**

*Eric L.*

**Signature of Witness      Date**

*陳盈智*

**Disclosure Submitted by**

**Inventor's Signature Date**

*陳盈智*

**Inventor's Signature Date**

*Ck chon*

**Inventor's Signature Date**

*JY Lee*

**Inventor's Signature Date**

*HT Lin*

# Invention Disclosure

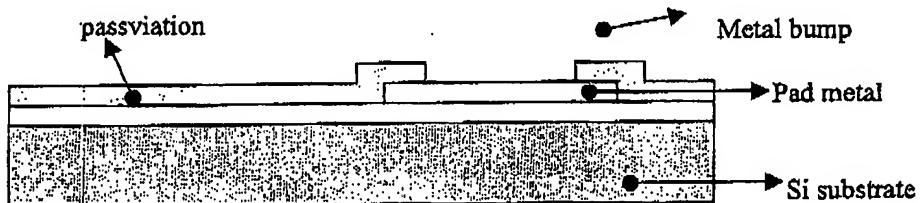
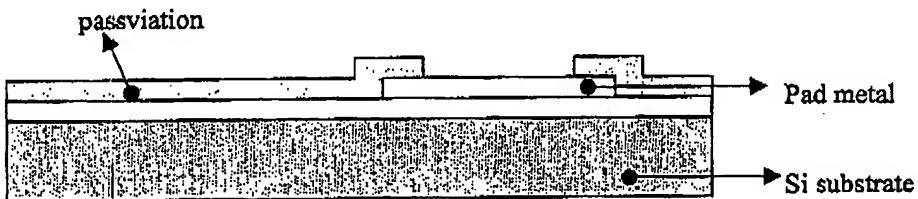
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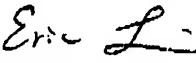
Detailed Description of Invention – Continued	For Use by IP Law Disclosure No. MEG02-005
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New invention:

\* After finish IC process

Add in a physical clean ex. Ar sputtering or ion mill to remove micro-contamination. The surface become very clean with no chemical absorption.



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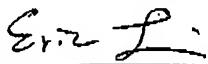
# Invention Disclosure

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Detailed Description of Invention – Continued	For Use by IP Law Disclosure No. MEG 02 -005
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## New invention:

The over kill problem will be eliminated during chip probing after this physical surface clean

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Invention Disclosure of Megic Corp. Page of Confidential When Completed

Full Name(s) of Inventor(s)		Employee No.	Department	Dept Code	Tel No. 310 13	For Use by IP Law
English	Chinese					MEG02-005 Received Date GEORGE O. SCHAFF & ASSOCIATES POUGHKEEPSIE, NY, U.S.A. (Name Stamp)

**Title of Invention –**

English: A Clean process for finishing IC product

Chinese

**Background Information – Current Practice and Disadvantages**

All the final process steps of metal pad or metal bump are chemical process in the current IC process.

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The physical clean can be a inner gas plasma, sputtering etch, ion mill or any bombardment clean.

**Problem Solved or Improvements Obtained by this Invention (Please List Item by Item)**

To reduce over killed problem during chip probing.

**Keyword Search for Patent/Literatures**

**Patent/Literatures Search Result (Please Specify Similar Patent No. and Literature Citation)**

**Detailed Description of Invention – (Continued Next Page)**

Please see next page

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Signature of Witness Date

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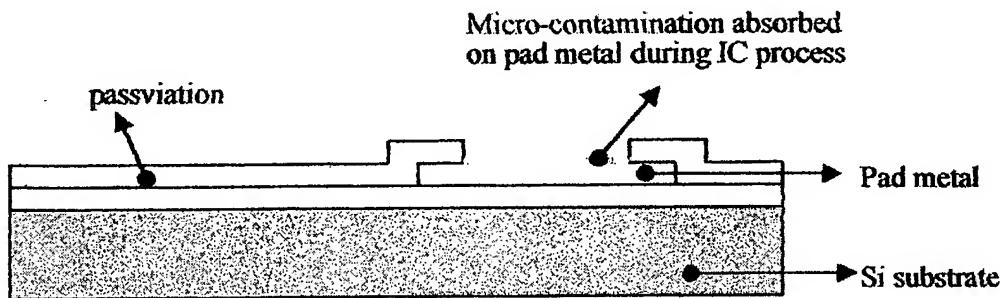
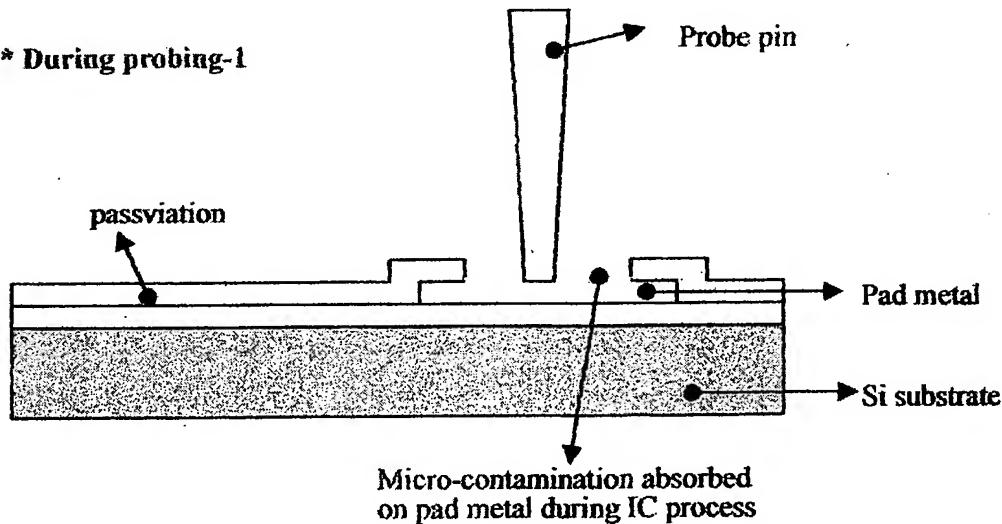
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Inventor's Signature Date

Inventor's Signature Date

Inventor's Signature Date

**Current practice 1:****\* After finish IC process****\* During probing-1**

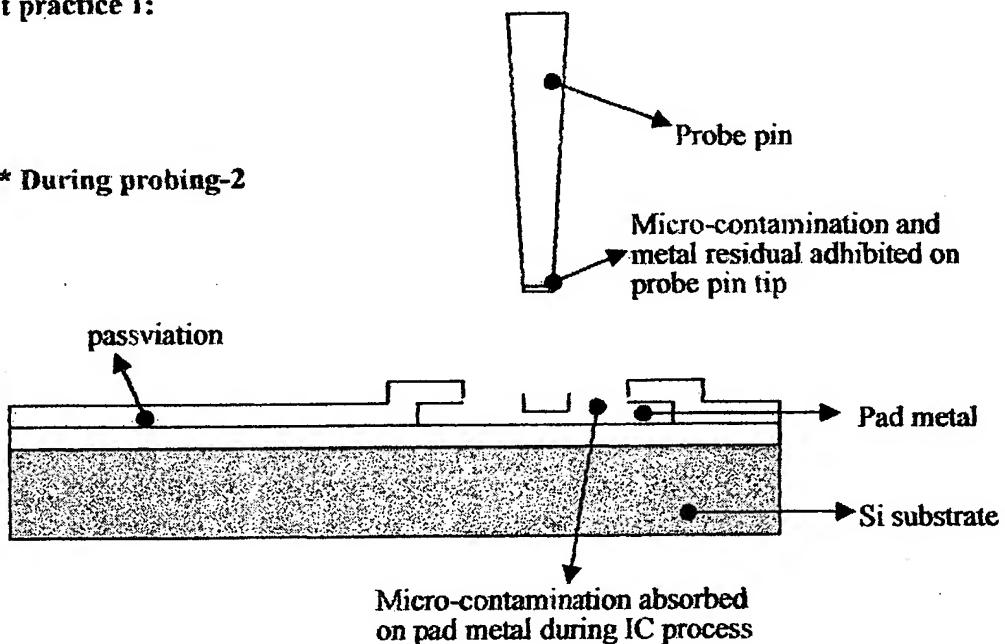
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**Disclosure Submitted by**

Inventor's Signature Date	Inventor's Signature Date
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**Signature of Witness Date**

**Current practice 1:****\* During probing-2**

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Signature of Witness Date

Inventor's Signature Date

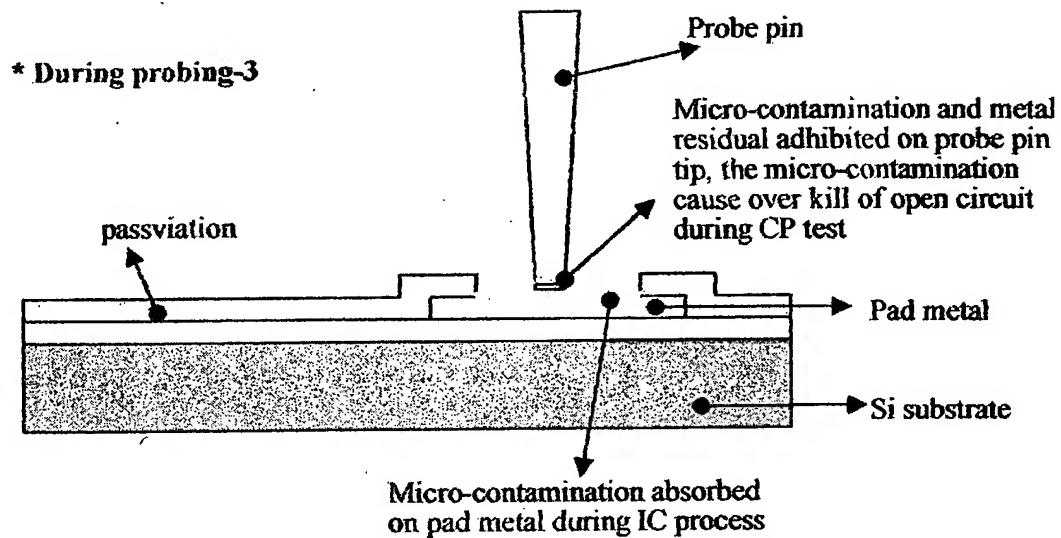
Inventor's Signature Date

Signature of Witness Date

Inventor's Signature Date

Inventor's Signature Date

Signature of Witness Date

**Current practice 1:**

**Witnesses: The Two Witnesses**  
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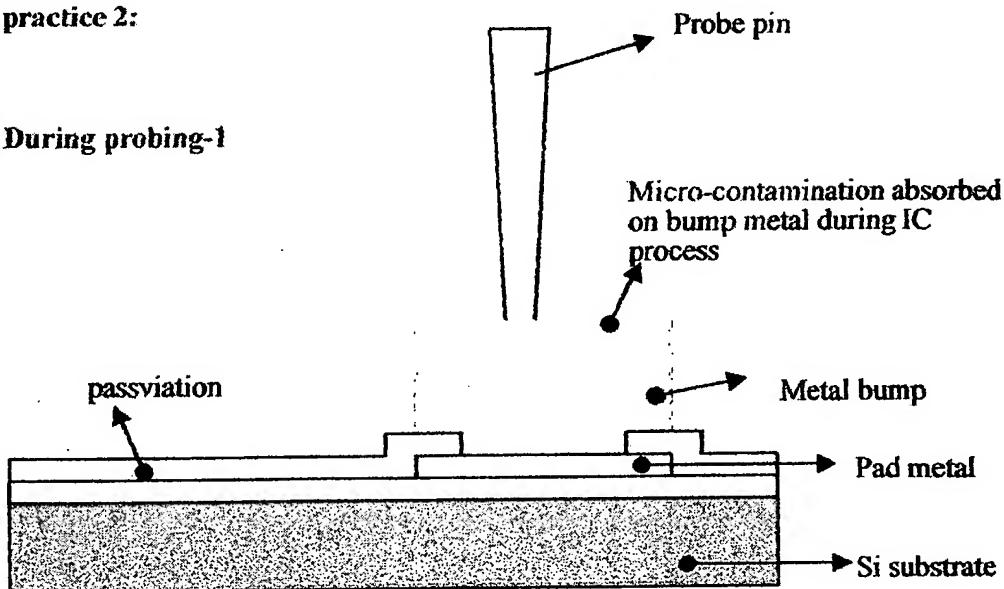
**Signature of Witness Date**

**Signature of Witness Date**

**Disclosure Submitted by**

Inventor's Signature Date	Inventor's Signature Date
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Inventor's Signature Date	Inventor's Signature Date
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**Current practice 2:****\* During probing-1**

**Witnesses: The Two Witnesses  
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Entire Invention Disclosure.**

**Signature of Witness Date**

**Signature of Witness Date**

**Disclosure Submitted by**

**Inventor's Signature Date**

**Inventor's Signature Date**

**Inventor's Signature Date**

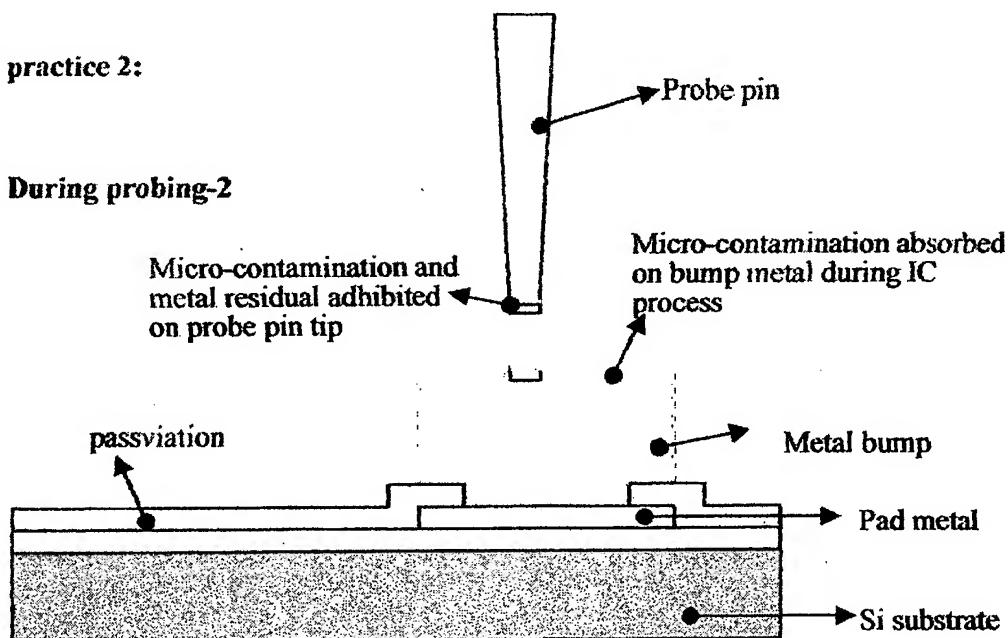
**Inventor's Signature Date**

Detailed Description of Invention – Continued

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**Current practice 2:**

**\* During probing-2**



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Signature of Witness Date

Disclosure Submitted by

Inventor's Signature Date

Inventor's Signature Date

Inventor's Signature Date

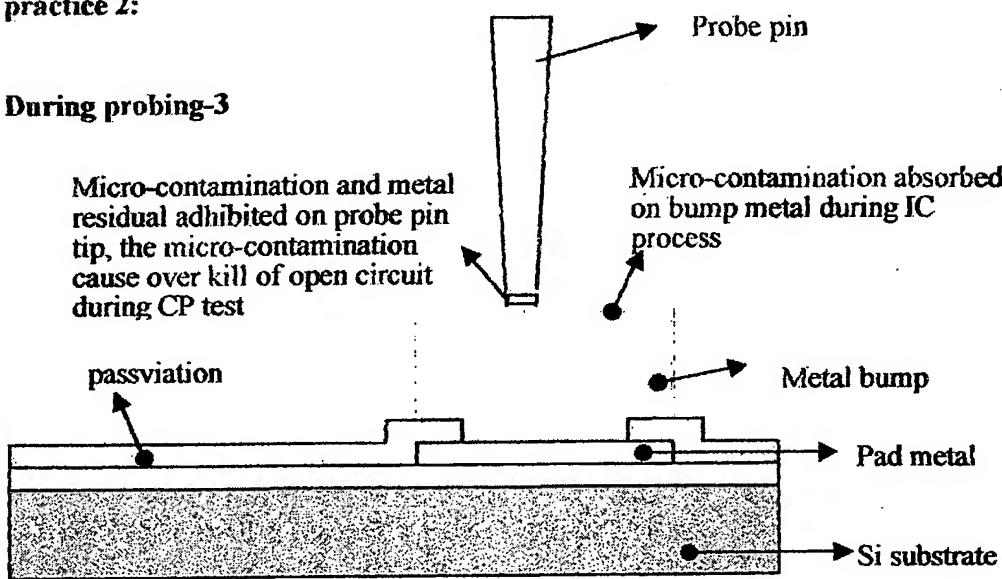
Inventor's Signature Date

Signature of Witness Date

**Current practice 2:**

\* During probing-3

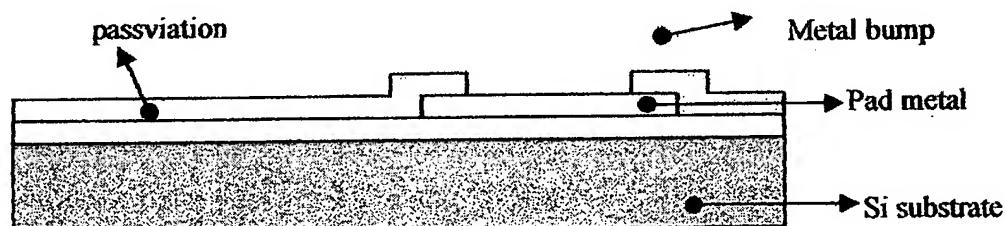
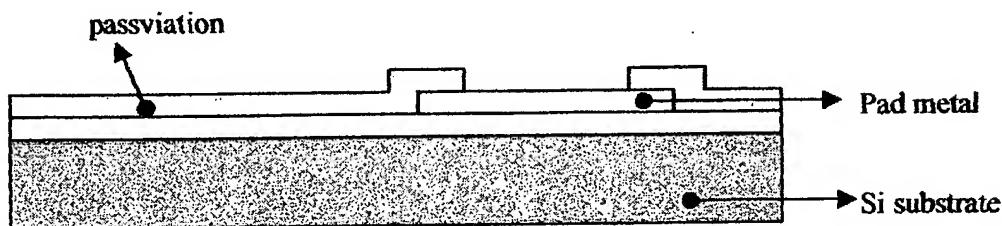
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Signature of Witness Date		
	Inventor's Signature Date	Inventor's Signature Date
Signature of Witness Date		

**New invention:****\* After finish IC process**

Add in a physical clean ex. Ar sputtering or ion mill to remove micro-contamination. The surface become very clean with no chemical absorption.



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**Signature of Witness Date**

**Disclosure Submitted by**

Inventor's Signature Date

Inventor's Signature Date

Inventor's Signature Date

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**New invention:**

The over kill problem will be eliminated during chip probing after  
this physical surface clean

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Signature of Witness Date		
Signature of Witness Date	Inventor's Signature Date	Inventor's Signature Date

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